

## S-Band, GaN/SiC, RF Power Transistor

2.7 - 2.9 GHz | 1500W | 58 % Efficiency typ | 15 dB Gain typ | 100 V | 50µs Pulse Length, 1% Duty Cycle

IGN2729M1500 and IGN2729M1500S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of modern radar systems. They supply a minimum of 1500W of peak output power, with typically 15dB of gain and 58% efficiency. They operate from a 100V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



### FEATURES

- GaN on SiC HEMT Technology
- Output Power >1500W
- Pre-matched Input and Output Impedances
- High Efficiency -58% typical
- 100% RF Tested under 50µs, 1% duty cycle pulse conditions
- RoHS and REACH Compliant

### APPLICATIONS

- S-band Radar Systems

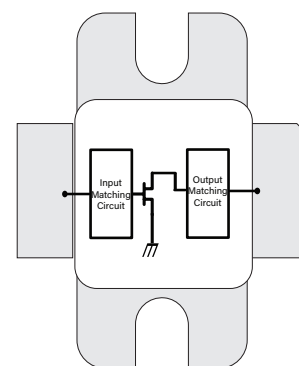


Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gain	G	13	15	17	dB	$P_{OUT} = 1500W$ $f = 2.7, 2.8, 2.9 \text{ GHz}$ 50µs pulse length, 1% duty cycle $V_{DS} = 100V, I_{DQ} = 50mA$
Drain Efficiency	$\eta$	50	58	65	%	
Pulse Droop	D	0	-0.4	-0.6	dB	
Input Return Loss	IRL	7	15	25	dB	
VSWR Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	5:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	$V_{DS}$	350	V	25 °C
DC Gate-Source Voltage	$V_{GS}$	-8 to +1	V	25 °C
DC Drain Current	$I_D$	54	A	25 °C
DC Gate Current	$I_G$	54	mA	25 °C
RF Input Power	$P_{RF,IN}$	90	W	25 °C
Operating Channel Temperature	$T_{CH}$	-55 to +225	°C	
Storage Temperature	$T_{STG}$	-55 to +150	°C	
Soldering Temperature	$T_{SOLDER}$	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

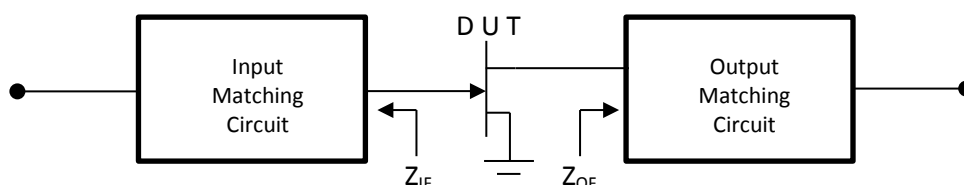
Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	$V_P$	-5.0			V	$V_{DS} = 100V, I_{DS} = 1mA$
Quiescent Gate Voltage	$V_Q$		-4.0		V	$V_{DS} = 100V, I_{DS} = 50mA$

Table 4. Thermal Resistance (Case temperature = 40°C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	$R_{TH}$		0.16		°C/W	$P_{diss} = 1086W$ 50µs pulse length, 1% duty cycle $V_{DS} = 100V$

Table 5. Matching Circuit Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (GHz)	$Z_{IF}$	$Z_{OF}$	Units	Test Conditions
2.7	6.6 - j4.9	3.9 - j3.3	$\Omega$	$P_{OUT} = 1500W$ 50µs Pulse length, 1% Duty Cycle $V_{DS} = 100V, I_{DQ} = 50mA$
2.8	6.3 - j4.6	3.7 - j2.4	$\Omega$	
2.9	5.9 - j4.2	3.5 - j1.5	$\Omega$	



TYPICAL RF PERFORMANCE

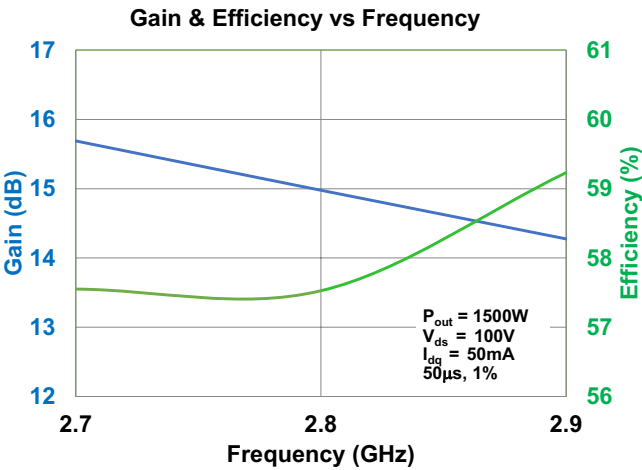


Figure 1

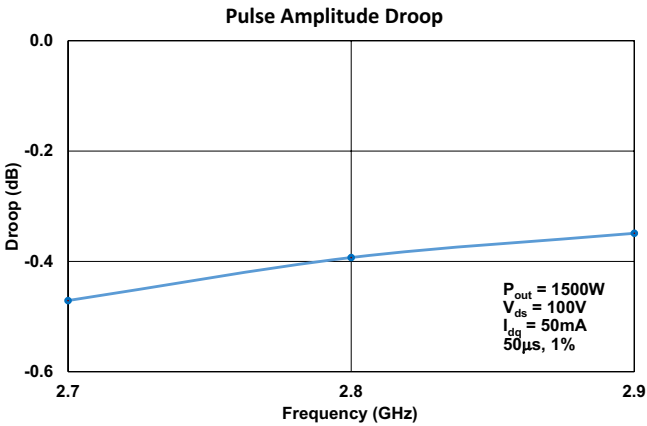


Figure 2

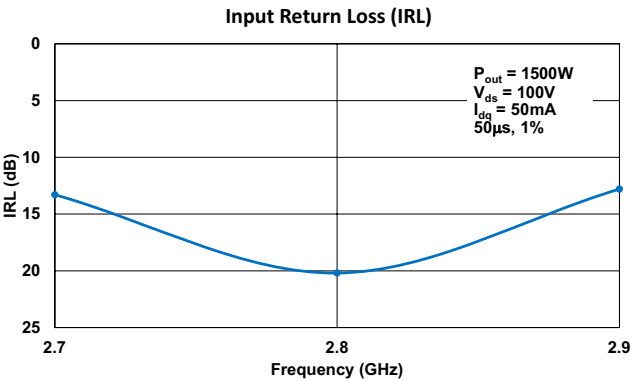
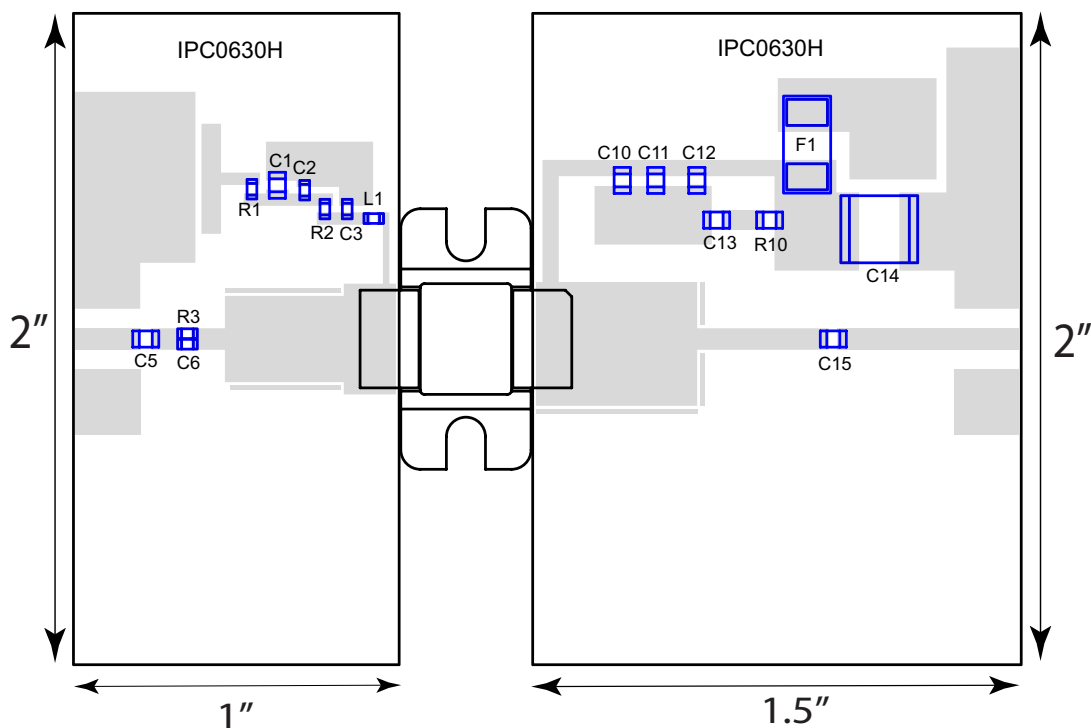


Figure 3

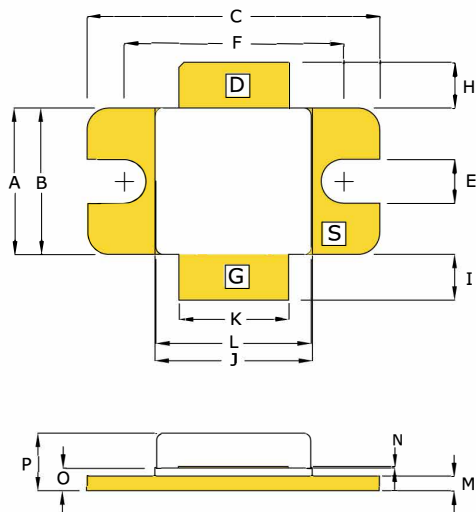
## TEST FIXTURE



### Bill of Materials for IGN2729M1500 Test Fixture

Designator	Description	Quantity	Part Number
C1	CAP 1000pF, 0805	1	08051A102JAR1-EM
C2	CAP 100pF, 0603	1	600S101JW250XT
C3	CAP 10pF, 0603	1	600S100FT250XT
C5, C10, C15	CAP, 18pF, 0805	3	600F180FT250XT
C6	CAP 18pF, 0603	1	600S180JT250XT
C11	CAP 100pF, 0805	1	600F101JT250XT
C12, C13	CAP 0.1μF, 0805	2	08051C104KAR1-EM
C14	CAP 10μF, 2220	1	KGM55CR72A106KV
L1	IND 6.8nH, 0603	1	0603HP-6N8XJRW
R1, R2	RES 5.1Ω, 0603	2	CRCW06035R11FKEA
R3	RES 100Ω, 0603	1	CRCW0603100RJNEAC
R10	RES 10Ω, 0805	1	CRCW080510R0JNEAC
F1	FUSE 10A	1	CB61F10A-TR1
PC Board	30 mils, 1oz/1oz Copper	2	RF-35TC-0300-E-C1/C1

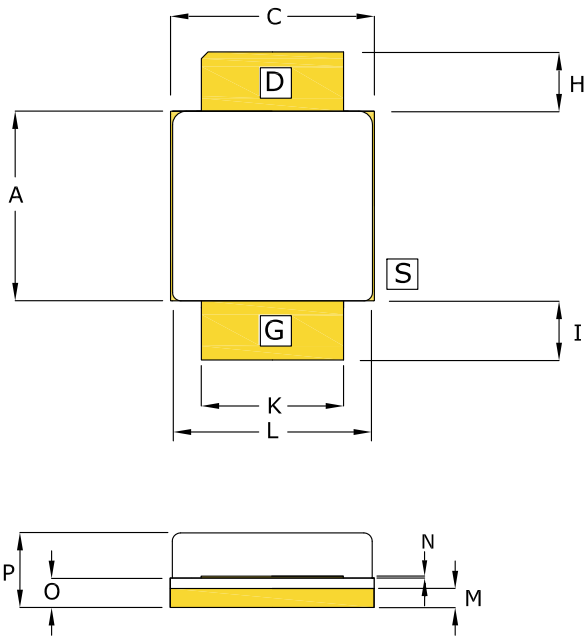
PACKAGE PL44E1



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.395	0.405	10.03	10.29
B	0.395	0.405	10.03	10.29
C	0.795	0.805	20.19	20.45
D	0.115	0.125	2.92	3.18
E	0.595	0.605	15.11	15.37
F	0.110	0.140	2.79	3.56
H	0.110	0.140	2.79	3.56
I	0.425	0.435	10.80	11.05
J	0.295	0.305	7.49	7.75
K	0.420	0.428	10.67	10.87
L	0.035	0.045	0.89	1.14
M	0.004	0.007	0.10	0.18
N	0.053	0.067	1.35	1.70
P	0.143	0.179	3.63	4.55

PIN	SCHEDULE
D	DRAIN
S	SOURCE
G	GATE

BOLT-DOWN FLANGE OPTION  
IGN2729M1500



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.393	0.408	9.97	10.35
B	--	--	--	--
C	0.423	0.438	10.73	11.11
D	--	--	--	--
E	--	--	--	--
F	--	--	--	--
H	0.110	0.140	2.79	3.56
I	0.110	0.140	2.79	3.56
J	--	--	--	--
K	0.295	0.305	7.49	7.75
L	0.420	0.428	10.67	10.87
M	0.035	0.045	0.89	1.14
N	0.004	0.007	0.10	0.18
O	0.053	0.067	1.35	1.70
P	0.143	0.179	3.63	4.55

PIN	SCHEDULE
D	DRAIN
S	SOURCE
G	GATE

EARLESS FLANGE OPTION  
IGN2729M1500S

### ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C11F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

### RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

### REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

### Disclaimer

Integra Technologies Inc. reserves the right to make changes without further notice to any products herein. Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale.

#### DEFINITIONS:

##### DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

**MAXIMUM RATINGS** Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865